

TABLE OF CONTENTS

Proceedings of the Fifth International Symposium on Low and High Dielectric Constant Materials:
Materials Science, Processing, and Reliability Issues

Preface

Symposium Chronology

Low Dielectric Constant Materials

Ultra Low K Dielectrics - Shortening the Time Line from R&D to Manufacturing - <i>B. Ahlburn, C. Hartfield, and T. Moore (Texas Instruments Incorporated)</i>	5
Deposition and Characterization of Perfluoro-Methyl Silica Films - <i>T. Fukumura, S. Sugahara, and M. Matsumura (Tokyo Institute of Technology)</i>	17
Characterization of Silica Films Having Olefin Groups - <i>K.-I. Usami, S. Sugahara, and M. Matsumura (Tokyo Institute of Technology)</i>	24
Integration Issues for New Dielectrics in CMOS Technology - <i>S. Gates, S.T. Chen, X. Chen, S. Cohen, D. Edelstein, J. Fitzsimmons, J. Hedrick, D. Restaino, J. Ryan, E. Simonyi, and S. Purushothaman (IBM)</i>	31
Effect of NH₃ Plasma Treatment on Improvement of Reliability of Cu/W-B-N/HSQ Interconnect Structures - <i>D.J. Kim (Hanyang University), H.S. Sim, Y.T. Kim (Korea Institute of Science and Technology), and J.-W. Park (Hanyang University)</i>	40
Low Dielectric Constant Material Deposited by HDPCVD for Barrier and Etch Stop Application in Cu Damascene Structure - <i>S.-M. Cho, L. Zhang, H. M'saad, and L. Zhuang (Applied Materials)</i>	48
Multiphase Low-k Materials Prepared by PECVD - <i>A. Grill and V. Patel (IBM Research Division)</i>	55
The Influence of Temperature on the Deposition of Low-k Films by PECVD of Trimethylsilane - <i>B.K. Hwang, M.J. Loboda, G. Cerny, R. Schneider, and J. Seifferly (Dow Corning Corporation)</i>	63
Enhancement of Organic Low-k Hybrid-Organic-Siloxane-Polymer (HOSP) in Resisting Oxygen Plasma Process - <i>T.-C. Chang (National Sun Yat-Sen University), P.-T. Liu, H. Su, C.-F. Chang (National Chiao Tung University), Y.-L. Yang, S. M. Sze (National Nano Device Laboratory), J. Hou, H. Chung (Allied Signal inc. Taiwan)</i>	72
A Study on the Formation and Characteristics of a-Fluorinated Carbon Films by CF₄/CH₄-ICPCVD - <i>M.S. Kang, K.S. Oh, C.K. Choi (Cheju National University), S.H. Um, and H.Y. Chang (Korea Advanced Institute of Science and Technology)</i>	90
Rapid Curing of Polymer Dielectrics by Variable Frequency Microwave Curing - <i>K. Farnsworth, R. Manepalli, S.A.B. Allen, and P. Kohl (Georgia Institute of Technology)</i>	103

Improvement in the Characteristics of Post-CMP Low-k Methylsilsesquioxane(MSQ)	114
- <i>T.-C. Chang (National Sun Yat-Sen University), P.-T. Liu, M.-C. Huang (National Chiao Tung University), T.-M. Tsai (National Tsing Hua University), K.-C. Hsu (National Chiao Tung University), Y.-L. Yang (National Nano Device Laboratory), S.M. Sze (National Chiao Tung University), H. Chung, and J. Hou (Allied Signal inc. Taiwan)</i>	
Ammonia Plasma Passivation Effects on Properties of Post-CMP Low-k Hydrogen Silsesquioxane (HSQ)	133
- <i>T.-C. Chang (National Sun Yat-Sen University), P.-T. Liu (National Chiao Tung University), T.-M. Tsai (National Tsing Hua University), C.-F. Chang (National Chiao Tung University), Y.-L. Yang (National Nano Device Laboratory), S.M. Sze (National Chiao Tung University), F.Y. Shih, E. Tsai, G. Chen, and J.K. Lee (Dow Corning Taiwan Inc.)</i>	
Post Etch Cleaning Solutions for the Integration of HOSPTM Low-k Dielectric,	144
- <i>O. Leonte, J. Dunne, N. Tadashi (Honeywell Electronic Materials)</i>	
Characterization of Ashing Effects on Low-k Dielectric Films	159
- <i>R.A. Shepherd, D. Nguyen (GaSonics International Corporation), G. Cerny, and M. J. Loboda (Dow Corning)</i>	
Electron Beam Curing of Thin Film Polymer Dielectrics	168
- <i>R. Manepalli, K. Farnsworth, S.A.B. Allen, and P. Kohl (Georgia Institute of Technology)</i>	
High Dielectric Constant Materials	
Influence of the Standard CMOS Processing on Ta₂O₅ Gate Dielectric Transistor Performance	178
- <i>G. Bersuker, M. Gilmer, P.M. Zeitzoff, G.A. Brown, M.D. Jackson, F. Shaapur, B. Foran, and H.R. Huff (SEMATECH)</i>	
Characterization of High-K Dielectrics Using the Non-Contact Surface Charge Profiler (SCP) Method	187
- <i>P. Roman, D. Lee (Penn State University), P. Mumbauer, R. Grant (PRIMAXX, Inc.), E. Kamieniecki (QC Solutions, Inc.), and J. Ruzylo (Penn State University)</i>	
Characterization of Gd₂O₃ Films Deposited on Si(100) by E-Beam Evaporation from Pressed-Powder Targets	193
- <i>D. Landheer, J. Gupta, J. Hulse, I. Sproule, J. McCaffrey, M. Graham (National Research Council of Canada), K.-C. Yang, Z. Lu (University of Toronto) and W. N. Lennard (University of Western Ontario)</i>	
Charge Transport in Anodized Ta₂O₅, HfO₂ and ZrO₂ Thin Films	205
- <i>C.D.W. Jones, R.M. Fleming, D.V. Lang, M.L. Steigerwald, D.W. Murphy, B. Vyas, G.B. Alers, Y.-H. Wong, R.B. van Dover, J.R. Kwo, and A.M. Sergent (Bell Labs - Lucent Technologies)</i>	
Processing Effects and Electrical Evaluation of ZrO₂ Formed by RTP Oxidation of Zr	214
- <i>R. Nieh, W.-J. Qi, B.H. Lee, L. Kang, Y. Jeon, K. Onishi, S. Gopalan, C.S. Kang, E. Dhrarmarajan, R. Choi, and J.C. Lee (University of Texas at Austin)</i>	
Low-Defect Anodized Ta For Use as a Dielectric in High Value Integrated Capacitors	222
- <i>R. Ulrich, Y. Xi, A. Date, M. Wasef, and R. Pandey (University of Arkansas)</i>	

Metal Electrode Challenges with the Emergence of High Permittivity Dielectric Materials - C. Hoover (<i>Praxair, Inc.</i>)	232
Studies of High-k Gate Dielectrics Deposited by the Liquid Source Misted Chemical Deposition Method - D. Lee, P. Roman (<i>Penn State University</i>), P. Mumbauer, R. Grant (<i>PRIMAXX, Inc.</i>), M. Horn, and J. Ruzylo (<i>Penn State University</i>)	237
Subject Index	243